

Xinjun Liu

List of Publications by Year in descending order

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84
papers

1,987
citations

236612

25
h-index

288905

40
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85
all docs

85
docs citations

85
times ranked

2021
citing authors

#	ARTICLE	IF	CITATIONS
1	Van der Pol oscillator based on NbO ₂ volatile memristor: A simulation analysis. Journal of Applied Physics, 2022, 131, 054501.	1.1	3
2	Modulation of magnetoresistance and field sensitivity of Co/ZnO nanocomposite film by microstructure controlling. Journal Physics D: Applied Physics, 2021, 54, 365003.	1.3	1
3	NbO ₂ Memristive Neurons for Burst-Based Perceptron. Advanced Intelligent Systems, 2020, 2, 2000066.	3.3	18
4	Schottky-Barrier-Induced Asymmetry in the Negative-Differential-Resistance Response of NbO_x Cross-Point Devices. Physical Review Applied, 2020, 12, 021101.	1.5	12
5	Spiking dynamic behaviors of NbO ₂ memristive neurons: A model study. Journal of Applied Physics, 2020, 127, .	1.1	11
6	Collective dynamics of capacitively coupled oscillators based on NbO ₂ memristors. Journal of Applied Physics, 2019, 126, 125112.	1.1	9
7	Origin of Current-Controlled Negative Differential Resistance Modes and the Emergence of Composite Characteristics with High Complexity. Advanced Functional Materials, 2019, 29, 1905060.	7.8	45
8	Current Localization and Redistribution as the Basis of Discontinuous Current Controlled Negative Differential Resistance in NbO _x . Advanced Functional Materials, 2019, 29, 1906731.	7.8	39
9	Photoassisted Electric Field Modulation of Multiple Nonvolatile Resistance States in Highly Strained Epitaxial BiFeO ₃ Heterostructures. Advanced Electronic Materials, 2018, 4, 1800171.	2.6	14
10	Anatomy of filamentary threshold switching in amorphous niobium oxide. Nanotechnology, 2018, 29, 375705.	1.3	36
11	Coupling dynamics of Nb/Nb ₂ O ₅ relaxation oscillators. Nanotechnology, 2017, 28, 125201.	1.3	28
12	Temperature dependent frequency tuning of NbO _x relaxation oscillators. Applied Physics Letters, 2017, 111, .	1.5	24
13	Threshold switching and electrical self-oscillation in niobium oxide films. Journal of Applied Physics, 2016, 120, .	1.1	67
14	Self-assembly of an NbO ₂ interlayer and configurable resistive switching in Pt/Nb/HfO ₂ /Pt structures. Applied Physics Letters, 2015, 107, .	1.5	21
15	Threshold current reduction for the metal-insulator transition in NbO ₂ -selector devices: the effect of ReRAM integration. Journal Physics D: Applied Physics, 2015, 48, 195105.	1.3	74
16	Effect of Electrode Roughness on Electroforming in HfO_2 Defect-Induced Moderation of Electric-Field Enhancement. Physical Review Applied, 2015, 4, .	1.5	38
17	High-endurance megahertz electrical self-oscillation in Ti/NbO _x bilayer structures. Applied Physics Letters, 2015, 106, .	1.5	44
18	Resistive switching behavior in HfO ₂ with Nb as an oxygen exchange layer. , 2014, , .		4

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37	Diode-less bilayer oxide (WO_x/NbO_x) device for cross-point resistive memory applications. <i>Nanotechnology</i> , 2011, 22, 475702.	1.3	81
38	Improved Resistive Switching Properties of Solution-Processed TiO_2 Film by Incorporating Atomic Layer Deposited TiO_2 layer. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 046504.	0.8	7
39	All-ZnO-based transparent resistance random access memory device fully fabricated at room temperature. <i>Journal Physics D: Applied Physics</i> , 2011, 44, 255104.	1.3	65
40	The unification of filament and interfacial resistive switching mechanisms for titanium dioxide based memory devices. <i>Journal of Applied Physics</i> , 2011, 109, 104504.	1.1	16
41	Improved resistive switching properties in Pt/Pr _{0.7} Ca _{0.3} MnO ₃ /Y ₂ O ₃ -stabilized ZrO ₂ /W via-hole structures. <i>Current Applied Physics</i> , 2011, 11, e58-e61.	1.1	20
42	Bipolar resistance switching in the Pt/WO _x /W nonvolatile memory devices. <i>Current Applied Physics</i> , 2011, 11, e62-e65.	1.1	17
43	Highly asymmetric bipolar resistive switching in solution-processed Pt/TiO ₂ /W devices for cross-point application. <i>Current Applied Physics</i> , 2011, 11, S102-S106.	1.1	23
44	Coexistence of filamentary and homogeneous resistive switching in graded WO_x thin films. <i>Physica Status Solidi - Rapid Research Letters</i> , 2011, 5, 89-91.	1.2	32
45	Memristive switching behavior in Pr _{0.7} Ca _{0.3} MnO ₃ by incorporating an oxygen-deficient layer. <i>Physica Status Solidi - Rapid Research Letters</i> , 2011, 5, 409-411.	1.2	19
46	Parallel memristive filaments model applicable to bipolar and filamentary resistive switching. <i>Applied Physics Letters</i> , 2011, 99, .	1.5	20
47	Structural properties and resistive switching behaviour in Mg _x Zn _{1-x} O alloy films grown by pulsed laser deposition. <i>Journal Physics D: Applied Physics</i> , 2011, 44, 015302.	1.3	5
48	Ferroelectric Polarization Effect on Al-Nb Codoped Pb(Zr _{0.52} Ti _{0.48})O ₃ /Pr _{0.7} Ca _{0.3} MnO ₃ Heterostructure Resistive Memory. <i>Electrochemical and Solid-State Letters</i> , 2011, 14, H225.	2.2	8
49	Realization of Rectifying and Resistive Switching Behaviors of TiO ₂ Nanorod Arrays for Nonvolatile Memory. <i>Electrochemical and Solid-State Letters</i> , 2011, 14, H422.	2.2	28
50	Characterization of Resistive Switching States in W/Pr _{0.7} Ca _{0.3} MnO ₃ for a Submicron (ϕ 250 nm) Via-Hole Structure. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 105802.	0.8	5
51	Resistive switching characteristics and mechanism of thermally grown WO _x thin films. <i>Journal of Applied Physics</i> , 2011, 110, .	1.1	65
52	Filament-Type Resistive Switching in Homogeneous Bi-Layer Pr _{0.7} Ca _{0.3} MnO ₃ Thin Film Memory Devices. <i>Electrochemical and Solid-State Letters</i> , 2011, 14, H9.	2.2	12
53	Resistive Switching Mechanism of a Pr _{0.7} Ca _{0.3} MnO ₃ -based Memory Device and Assessment of Its Suitability for Nano-scale Applications. <i>Journal of the Korean Physical Society</i> , 2011, 59, 497-500.	0.3	11
54	Characterization of Resistive Switching States in W/Pr _{0.7} Ca _{0.3} MnO ₃ for a Submicron (ϕ 250 nm) Via-Hole Structure. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 105802.	0.8	3

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55	Asymmetric bipolar resistive switching in solution-processed Pt/TiO ₂ /W devices. Journal Physics D: Applied Physics, 2010, 43, 495104.	1.3	35
56	Improved resistive switching properties in stacked structures. Solid State Communications, 2010, 150, 137-141.	0.9	15
57	Low programming voltage resistive switching in reactive metal/polycrystalline Pr _{0.7} Ca _{0.3} MnO ₃ devices. Solid State Communications, 2010, 150, 2231-2235.	0.9	36
58	Interfacial resistive switching properties in Ti/La _{0.7} Ca _{0.3} MnO ₃ /Pt sandwich structures. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1204-1209.	0.8	15
59	Improved Resistive Switching Properties of Solution Processed TiO ₂ Thin Films. Electrochemical and Solid-State Letters, 2010, 13, H443.	2.2	8
60	Improving the Oxygen Permeability of Ba _{0.5} Sr _{0.5} Co _{0.8} Fe _{0.2} O _{3-λ} Membranes by Laser Ablation. Wuji Cailiao Xuebao/Journal of Inorganic Materials, 2010, 25, 221-224.	0.6	0
61	The polarity origin of the bipolar resistance switching behaviors in metal/La _{0.7} Ca _{0.3} MnO ₃ /Pt junctions. Applied Physics Letters, 2009, 95, .	1.5	46
62	The Effect of Oxygen Annealing on the Resistance Switching Properties of the La _{0.7} Ca _{0.3} MnO ₃ Films. Advanced Materials Research, 2009, 66, 127-130.	0.3	0
63	Stable bipolar resistance switching behaviour induced by a soft breakdown process at the Al/La _{0.7} Ca _{0.3} MnO ₃ interface. Journal Physics D: Applied Physics, 2009, 42, 175408.	1.3	22
64	Multiform Resistance Switching Effects in the Al/La _{0.7} Ca _{0.3} MnO ₃ /Pt Structure. Electrochemical and Solid-State Letters, 2009, 12, H281.	2.2	11
65	Bipolar resistive switching properties of microcrystalline TiO ₂ thin films deposited by pulsed laser deposition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 157, 36-39.	1.7	15
66	Electric-field-induced resistance behavior in Ag/Pr _{1-x} Ca _x MnO ₃ /Pt (x=0,0.3,1.0) heterostructures. Applied Physics A: Materials Science and Processing, 2009, 96, 643-653.	1.1	2
67	Resistance-switching properties of La _{0.67} Ca _{0.33} MnO ₃ thin films with Ag-Al alloy top electrodes. Applied Physics A: Materials Science and Processing, 2009, 97, 85-90.	1.1	11
68	Effects of the compliance current on the resistive switching behavior of TiO ₂ thin films. Applied Physics A: Materials Science and Processing, 2009, 97, 883-887.	1.1	58
69	Structural characteristics and resistive switching properties of thermally prepared TiO ₂ thin films. Journal of Alloys and Compounds, 2009, 486, 458-461.	2.8	19
70	Forming-free colossal resistive switching effect in rare-earth-oxide Gd ₂ O ₃ films for memristor applications. Journal of Applied Physics, 2009, 106, .	1.1	126
71	The in-plane magnetic anisotropy of RF-sputtered FeNiN thin films. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 350-356.	0.8	3
72	Reversible change in magnetic moment and specific heat of La _{0.9} Ca _{0.1} MnO ₃ at different resistance states. Journal Physics D: Applied Physics, 2008, 41, 115001.	1.3	5

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73	Improvement of resistive switching property in a noncrystalline and low-resistance $\text{La}_{0.7}\text{Ca}_{0.3}\text{MnO}_3$ thin film by using an Ag/Al alloy electrode. <i>Journal Physics D: Applied Physics</i> , 2008, 41, 215409.	1.3	15
74	The effect of Fe doping on structural, magnetic and electrical transport properties of $\text{CaMn}_{1-x}\text{Fe}_x\text{O}_3$ ($x=0-0.35$). <i>Solid State Communications</i> , 2007, 142, 525-530.	0.9	18
75	Charge ordering characteristics in $\text{Y}_{0.5}\text{Ca}_{0.5}\text{MnO}_3$ manganite. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 2007, 370, 512-516.	0.9	3
76	Magnetic, electrical transport and electron spin resonance studies of Fe-doped manganite $\text{LaMn}_{0.7}\text{Fe}_{0.3}\text{O}_3$. <i>Journal of Magnetism and Magnetic Materials</i> , 2007, 313, 354-360.	1.0	25
77	Magnetic, electrical transport and electron spin resonance studies of ferromagnetic insulating manganites $\text{Nd}_{0.85}\text{Na}_{0.15}\text{MnO}_3$. <i>Journal of Magnetism and Magnetic Materials</i> , 2006, 305, 352-356.	1.0	1
78	Bulk $\text{Sn}_{1-x}\text{Mn}_x\text{O}_2$ magnetic semiconductors without room-temperature ferromagnetism. <i>Solid State Communications</i> , 2006, 138, 175-178.	0.9	25
79	Magnetic and electronic properties of charge ordered $\text{Nd}_{0.8}\text{Na}_{0.2}\text{MnO}_3$. <i>Journal of Magnetism and Magnetic Materials</i> , 2004, 284, 133-139.	1.0	18
80	Magnetic, electrical transport and electron spin resonance studies of charge-ordered $\text{Nd}_{0.75}\text{Na}_{0.25}\text{MnO}_3$. <i>Physica B: Condensed Matter</i> , 2004, 348, 146-150.	1.3	14
81	Magnetic properties of the charge ordered $\text{Nd}_{0.75}\text{Na}_{0.25}\text{MnO}_3$. <i>Solid State Communications</i> , 2004, 130, 563-566.	0.9	14
82	Competition between the charge ordered and ferromagnetic states in $(\text{La},\text{Nd})_{0.75}\text{Na}_{0.25}\text{MnO}_3$ manganites. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 2004, 325, 430-434.	0.9	9
83	Fabrication and Resistance-Switching Behaviors of NiO Thin Films by Thermal Oxidation of Evaporated Ni Films. <i>Advanced Materials Research</i> , 0, 66, 131-134.	0.3	1
84	Understanding composite negative differential resistance in niobium oxide memristors. <i>Journal Physics D: Applied Physics</i> , 0, , .	1.3	5